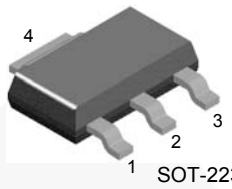
November 2014

NZT651
NPN Current Driver Transistor

Description

This device is designed for power amplifier, regulator and switching circuits where speed is important. Sourced from process 4P.



SOT-223

1. Base 2,4. Collector 3. Emitter

Ordering Information

Part Number	Marking	Package	Packing Method
NZT651	651	SOT-223 4L	Tape and Reel

Absolute Maximum Ratings[1],[2]

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	60	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	4.0	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

1. These ratings are based on a maximum junction temperature of 150°C.
2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

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Thermal Characteristics[3]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Max.	Unit
P_D	Total Power Dissipation	1.2	W
	Derate Above 25°C	9.7	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	103	°C/W

Note:

3. Device is mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead minimum 6 cm^2.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C = 10 mA, I_B = 0	60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 100 μA, I_E = 0	80		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 100 μA, I_C = 0	5.0		V
I_{CBO}	Collector Cut-Off Current	V_{CB} = 80 V, I_E = 0		100	nA
I_{EBO}	Emitter Cut-Off Current	V_{EB} = 4.0 V, I_C = 0		0.1	μA
h_{FE}	DC Current Gain[4]	I_C = 50 mA, V_{CE} = 2.0 V	75		
		I_C = 500 mA, V_{CE} = 2.0 V	75		
		I_C = 1.0 A, V_{CE} = 2.0 V	75		
		I_C = 2.0 A, V_{CE} = 2.0 V	40		
V_{CE}(sat)	Collector-Emitter Saturation Voltage[4]	I_C = 1.0 A, I_B = 100 mA		0.3	V
		I_C = 2.0 A, I_B = 200 mA		0.5	
V_{BE}(sat)	Base-Emitter Saturation Voltage[4]	I_C = 1.0 A, I_B = 100 mA		1.2	V
V_{BE}(on)	Base-Emitter On Voltage[4]	I_C = 1.0 A, V_{CE} = 2.0 V		1.0	V
f_T	Current Gain - Bandwidth Product	I_C = 50 mA, V_{CE} = 5.0 V, f = 100 MHz	75		MHz

Note:

4. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2.0%

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Typical Performance Characteristics

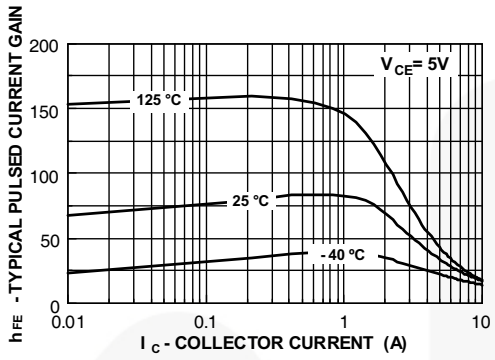

Figure 1. Typical Pulsed Current Gain vs. Collector Current

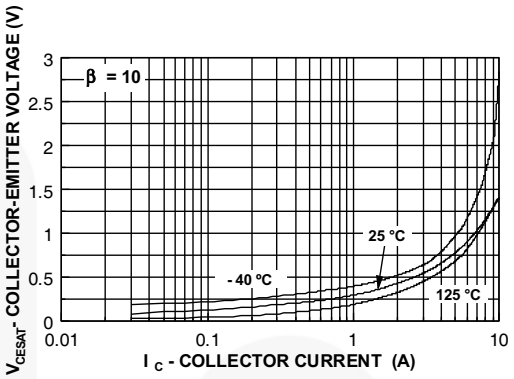

Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

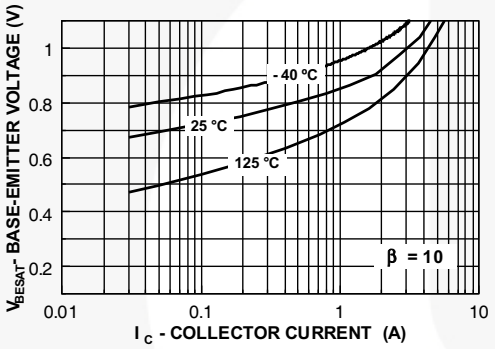

Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

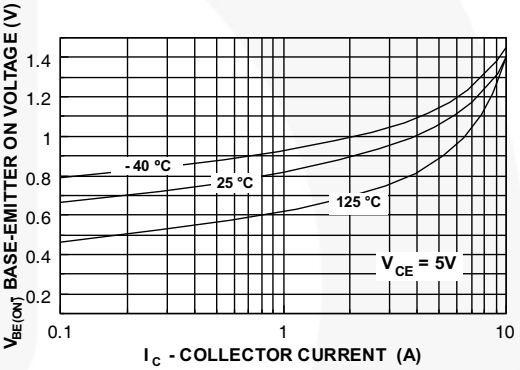

Figure 4. Base-Emitter On Voltage vs. Collector Current

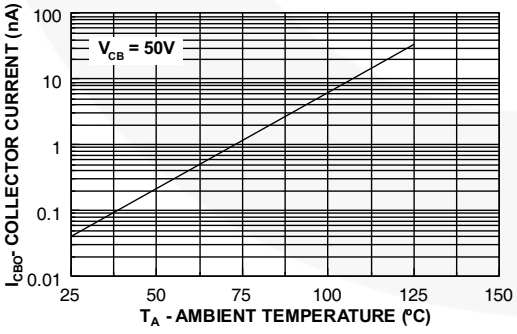

Figure 5. Collector Cut-Off Current vs. Ambient Temperature

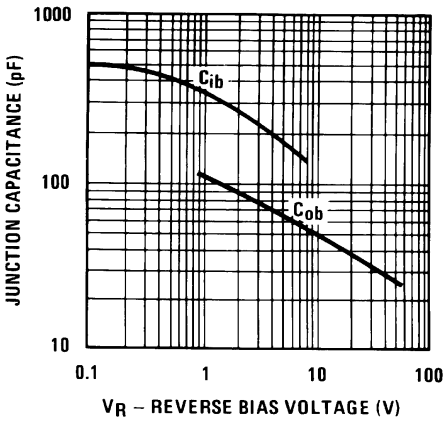

Figure 6. Junction Capacitance vs. Reverse Bias Voltage

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Typical Performance Characteristics (Continued)

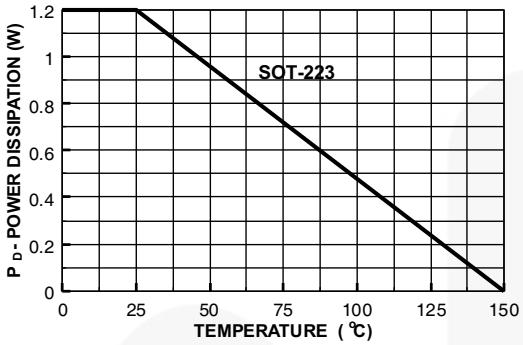

Figure 7. Power Dissipation vs. Ambient Temperature

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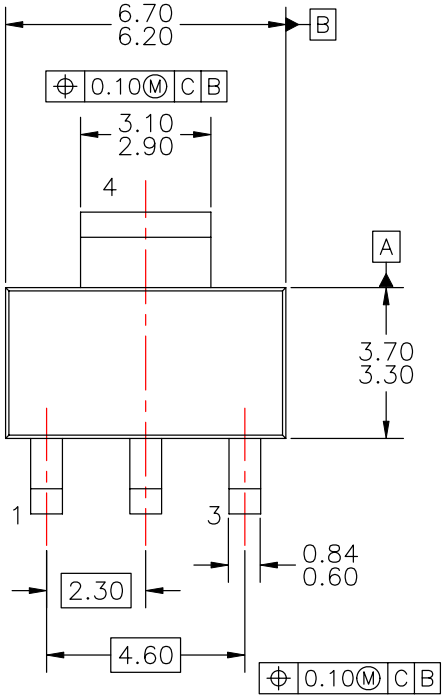
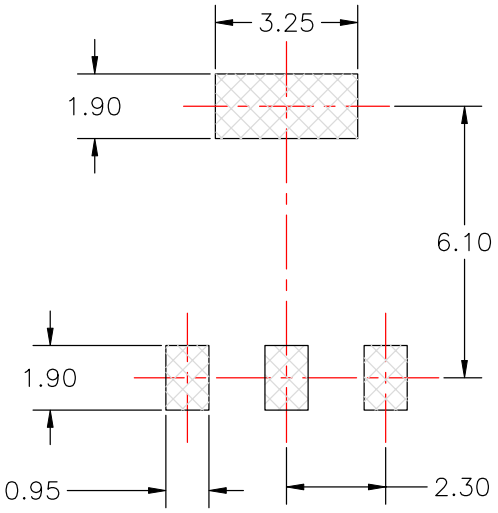
APPROVED
July-14-2008

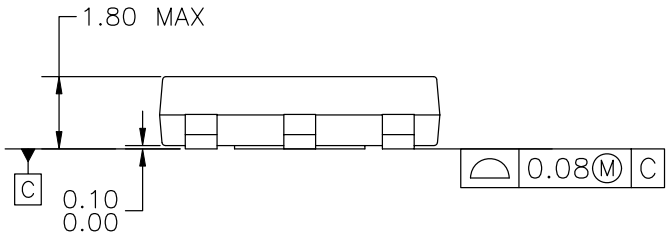
REVISIONS

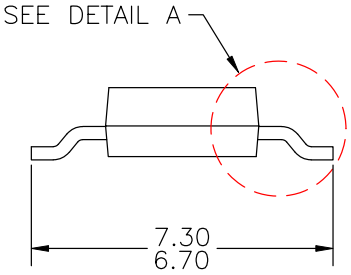
LTR	DESCRIPTION	DATE	NAME/SITE
A	RELEASE TO DOCUMENT CONTROL	JAN.25,1996	TL/FSCP
2	CHG DWG TEMPLATE FR NATIONAL TO FAIRCHILD; CHG DIM STYLE FR DUAL INCH[MM] TO SINGLE, MM; CHG LD WID FR $0.74^{+0.05}_{-0.07}$ TO 0.60–0.84; REMOVE PKG THICK DIM (1.6); CHG TOTAL PKG HT FR $1.80^{}_{1.50}$ TO 1.80 MAX; CHG FOOT LANDING DIM FR 0.91 MIN TO 0.60 MIN; CHG LD THICKNESS FR $0.3^{+0.09}_{-0.07}$ TO 0.20–0.35; ADD DRAFT ANGLE OF MOLDED BODY TOP & BOT; CHG LD LGTH TO PKG EDGE DIM TO BASIC; CHG LD PITCH FR 2.29 BS TO 2.30 BS; CHG BODY WID FR $3.56^{+0.18}_{-0.38}$ TO $^{3.70}_{3.30}$; CHG BODY LN FR $6.5^{+0.3}_{-0.4}$ TO $^{6.70}_{6.30}$; CHG TOTAL PKG WID FR $6.96^{+0.33}_{-0.38}$ TO $^{7.30}_{6.70}$; CHG PAD SIZE FR 0.99 MAX TO 0.95; CHG PAD PITCH FR 2.286 TO 2.30; CHG THERMAL TAB SIZE FR 3.28 MAX TO 3.25; CHG PAD SIZE FR 1.5 TO 1.90; CHG PAD SPACE FR 6.3 TO 6.10; CHG NOTE '2' TO 'A' W/O DATE; DEL NOTE ON LD FINISH; ADD NOTES B, C, D, E & F.	12FEB08	LZSC/FSCP

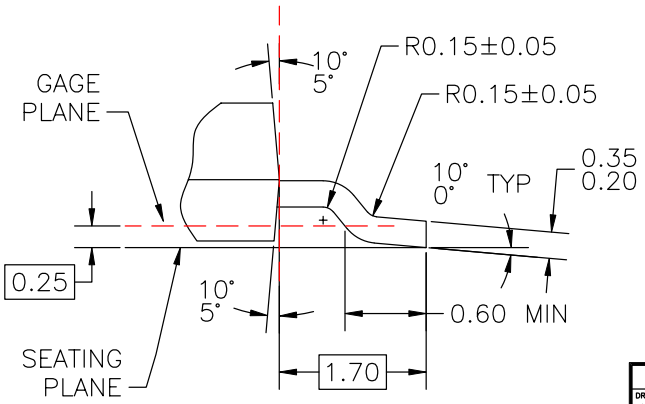




LAND PATTERN RECOMMENDATION







DETAIL A
SCALE: 2:1

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C) ALL DIMENSIONS ARE IN MILLIMETERS.
D) DRAWING CONFORMS TO ASME Y14.5M–1994.
E) LANDPATTERN NAME: SOT230P700X180–4BN
F) DRAWING FILENAME: MKT–MA04AREV2

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DRAWN: J.U. COMPARATIVO JR.	26FEB2008
CHECKED: L.Z. STA CRUZ	
APPROVED: M.R. GESTOLE	
G.S. BAJE	

PROJECTION INCH [MM]

FAIRCHILD SEMICONDUCTOR TM

MOLDED PACKAGE
SOT–223, 4 LEAD

SCALE	SIZE	DRAWING NUMBER	REV
1:1	A3	MKT–MA04A	2

FORMERLY: N/A SHEET : 1 OF 1

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